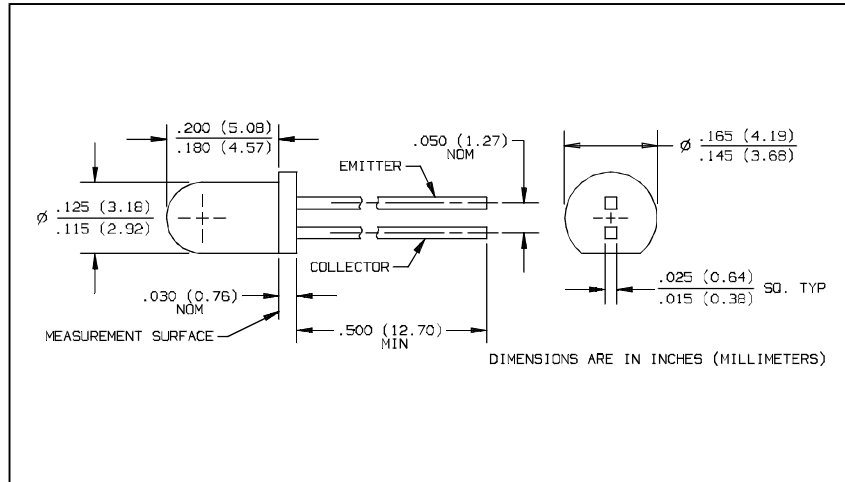




Product Bulletin OP705
March 1999

NPN Phototransistor with Base-Emitter Resistor Types OP705A, OP705B, OP705C, OP705D



Features

- Narrow receiving angle
- Variety of sensitivity ranges
- T-1 package style
- Small package size for space limited applications
- Base-emitter resistor provides ambient light protection

Description

The OP705 series devices consist of NPN silicon phototransistors molded in blue tinted epoxy packages. The narrow receiving angle provides excellent on-axis coupling. These devices are 100% production tested using infrared light for close correlation with Optek's GaAs and GaAlAs emitters.

The phototransistor has an internal base-emitter resistor which provides protection from low level ambient lighting conditions. This feature is also useful when the media being detected is semi-transparent to infrared light in interruptive applications.

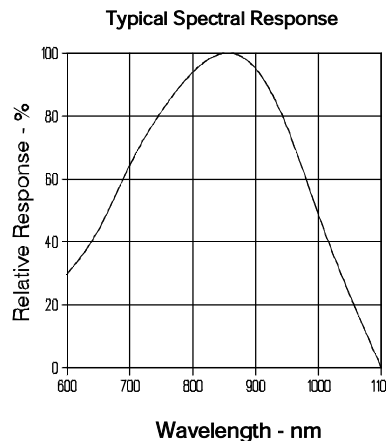
Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Collector-Emitter Voltage.....	30 V
Emitter Reverse Current.....	10 mA
Collector DC Current.....	30 mA
Storage and Operating Temperature Range.....	-40° C to +100° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron].....	260° C ⁽¹⁾
Power Dissipation.....	100 mW ⁽²⁾

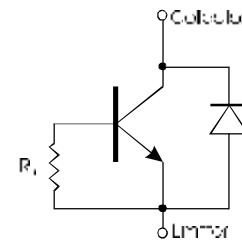
Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. Max. 20 grams force may be applied to leads when soldering.
- (2) Derate linearly 1.33 mW/° C above 25° C.
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the phototransistor being tested.
- (4) The knee point irradiance is defined as the irradiance required to increase I_{C(O/N)} to 50• A.

Typical Performance Curves



Schematic



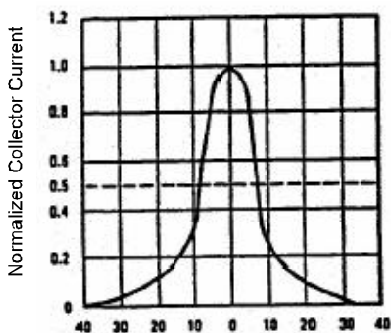
Types OP705A, OP705B, OP705C, OP705D

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
$I_{C(ON)}$	On-State Collector Current	OP705A	3.95		12.0	mA	$V_{CE} = 5\text{ V}$, $E_e = .50\text{ mW/cm}^{2(3)}$
		OP705B	2.65		7.25		
		OP705C	1.50		4.85		
		OP705D	1.50		12.0		
E_{KP}	Knee Point Irradiance		.02		mW/cm ²	$V_{CE} = 5\text{ V}^{(4)}$	
I_{CEO}	Collector-Emitter Dark Current			100	nA	$V_{CE} = 10\text{ V}$, $E_e = 0$	
I_{ECO}	Emitter-Reverse Current			100	μA	$V_{EC} = 0.4\text{ V}$	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30			V	$I_C = 100\ \mu\text{A}$	
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage			0.4	V	$I_C = 250\ \mu\text{A}$, $E_e = .50\text{ mW/cm}^{2(3)}$	

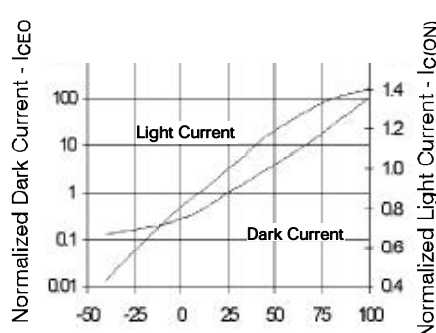
Typical Performance Curves

Normalized Collector Current vs. Angular Displacement



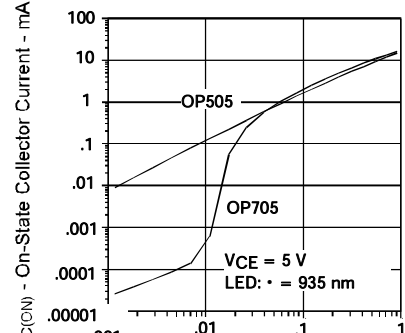
• - Angular Displacement - Deg.

Normalized Light and Dark Current vs. Ambient Temperature



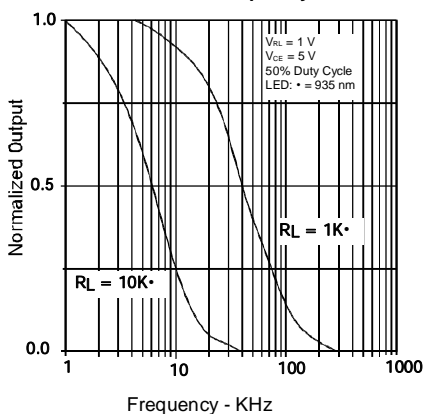
T_A - Ambient Temperature - °C

On-State Collector Current vs. Irradiance

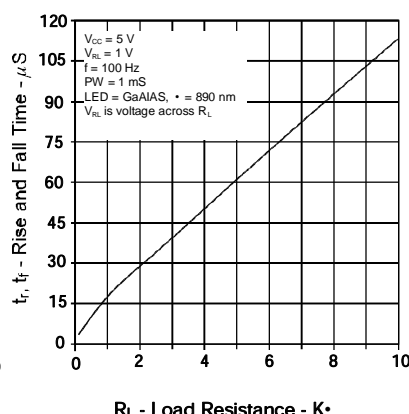


E_e - Irradiance - mW/cm²

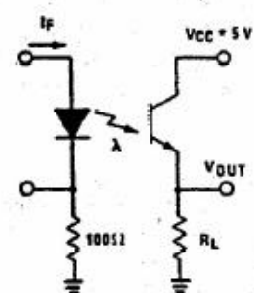
Normalized Output vs. Frequency



Typical Rise and Fall Time vs. Load Resistance



Switching Time Test Circuit



Test Conditions:
Light source is pulsed LED with t_r and $t_f = 500\text{ ns}$.
 I_f is adjusted for $V_{OUT} = 1\text{ Volt}$.

Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.
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